



## SI2302

### Features

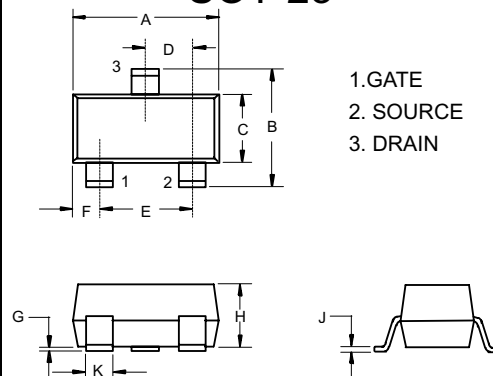
- 20V, 3.0A,  $R_{DS(ON)} = 55m\Omega$  @  $V_{GS} = 4.5V$   
 $R_{DS(ON)} = 82m\Omega$  @  $V_{GS} = 2.5V$
- High dense cell design for extremely low  $R_{DS(ON)}$
- Rugged and reliable
- Lead free product is acquired
- SOT-23 Package
- Marking Code: S2
- Epoxy meets UL 94 V-0 flammability rating
- Moisture Sensitivity Level 1

#### Maximum Ratings @ 25°C Unless Otherwise Specified

Symbol	Parameter	Rating	Unit
$V_{DS}$	Drain-source Voltage	20	V
$I_D$	Drain Current-Continuous	3	A
$I_{DM}$	Drain Current-Pulsed <sup>a</sup>	10	A
$V_{GS}$	Gate-source Voltage	$\pm 8$	V
$P_D$	Total Power Dissipation	1.25	W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient <sup>b</sup>	100	°C/W
$T_J$	Operating Junction Temperature	-55 to +150	°C
$T_{STG}$	Storage Temperature	-55 to +150	°C

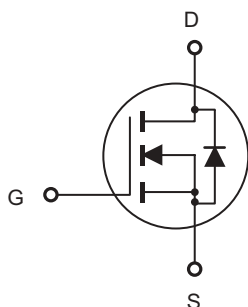
### N-Channel Enhancement Mode Field Effect Transistor

#### SOT-23

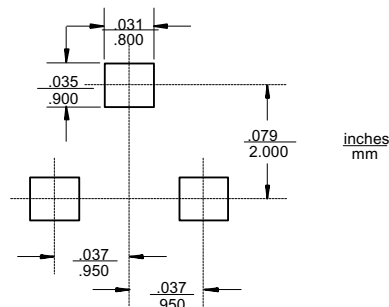


DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	.110	.120	2.80	3.04	
B	.083	.098	2.10	2.64	
C	.047	.055	1.20	1.40	
D	.035	.041	.89	1.03	
E	.070	.081	1.78	2.05	
F	.018	.024	.45	.60	
G	.0005	.0039	.013	.100	
H	.035	.044	.89	1.12	
J	.003	.007	.085	.180	
K	.015	.020	.37	.51	

### Internal Block Diagram



#### Suggested Solder Pad Layout





Micro Commercial Components

# SI2302

## Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 10μA	20			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V			1	μA
Gate Body Leakage Current, Forward	I <sub>GSSF</sub>	V <sub>GS</sub> = 8V, V <sub>DS</sub> = 0V			100	nA
Gate Body Leakage Current, Reverse	I <sub>GSSR</sub>	V <sub>GS</sub> = -8V, V <sub>DS</sub> = 0V			-100	nA
On Characteristics <sup>c</sup>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 50μA	0.65		1.2	V
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 3.6A		55	72	mΩ
On-Resistance		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 3.1A		82	110	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> = 5V, I <sub>D</sub> = 3.6A		8.5		S
Dynamic Characteristics <sup>d</sup>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V, f = 1.0 MHz		237		pF
Output Capacitance	C <sub>oss</sub>			120		pF
Reverse Transfer Capacitance	C <sub>rss</sub>			45		pF
Switching Characteristics <sup>d</sup>						
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 10V, I <sub>D</sub> = 3.6A, V <sub>GS</sub> = 4.5V, R <sub>GEN</sub> = 6Ω		23	45	ns
Turn-On Rise Time	t <sub>r</sub>			11	30	ns
Turn-Off Delay Time	t <sub>d(off)</sub>			34	70	ns
Turn-On Fall Time	t <sub>f</sub>			36	70	ns
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = 10V, I <sub>D</sub> = 3.6A, V <sub>GS</sub> = 4.5V		6	10	nC
Gate-Source Charge	Q <sub>gs</sub>			1.4		nC
Gate-Drain Charge	Q <sub>gd</sub>			1.8		nC
Drain-Source Diode Characteristics and Maximun Ratings						
Drain-Source Diode Forward Current <sup>b</sup>	I <sub>S</sub>				0.94	A
Drain-Source Diode Forward Voltage <sup>c</sup>	V <sub>SD</sub>	V <sub>GS</sub> = 0V, I <sub>S</sub> = 0.94A			1.2	V
Notes : a.Repetitive Rating : Pulse width limited by maximum junction temperature. b.Surface Mounted on FR4 Board, t ≤ 10 sec. c.Pulse Test : Pulse Width ≤ 300μs, Duty Cycle ≤ 2%. d.Guaranteed by design, not subject to production testing.						

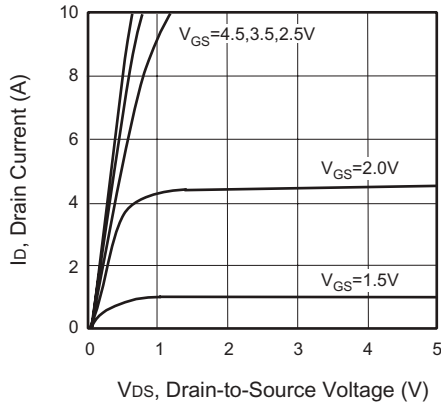


Figure 1. Output Characteristics

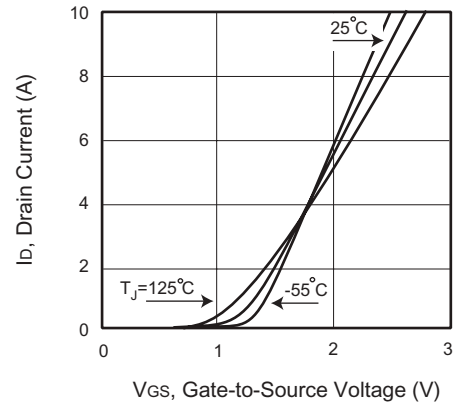


Figure 2. Transfer Characteristics

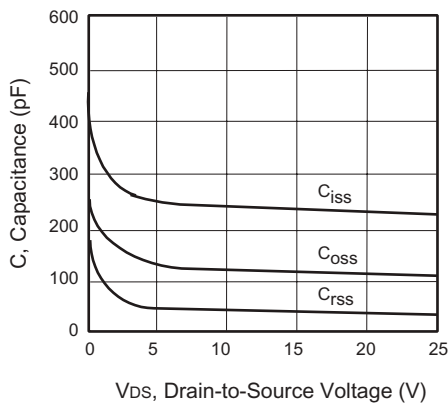


Figure 3. Capacitance

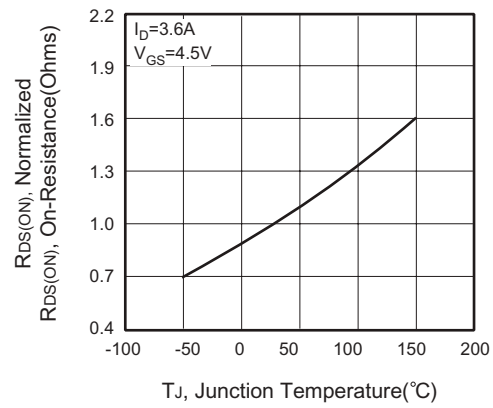


Figure 4. On-Resistance Variation with Temperature

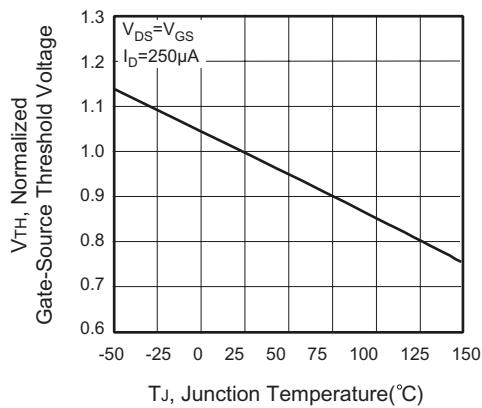


Figure 5. Gate Threshold Variation with Temperature

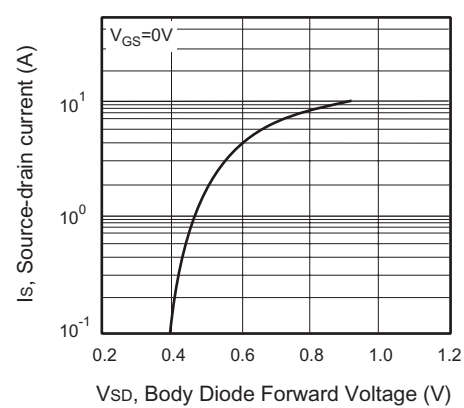


Figure 6. Body Diode Forward Voltage Variation with Source Current

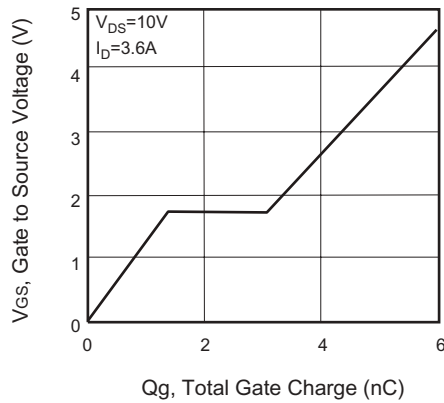


Figure 7. Gate Charge

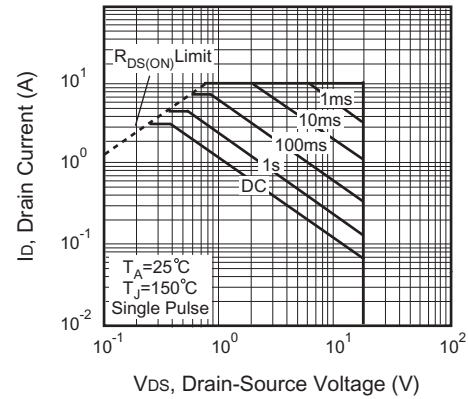


Figure 8. Maximum Safe Operating Area

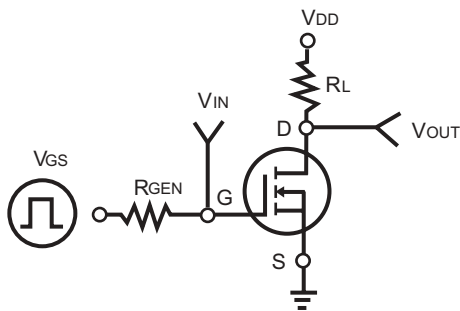


Figure 9. Switching Test Circuit

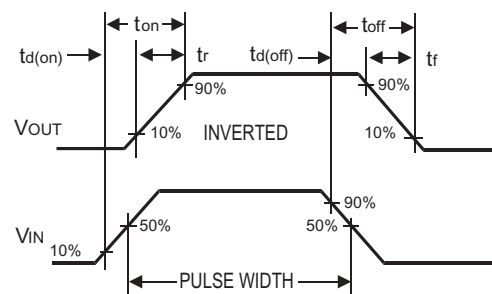


Figure 10. Switching Waveforms

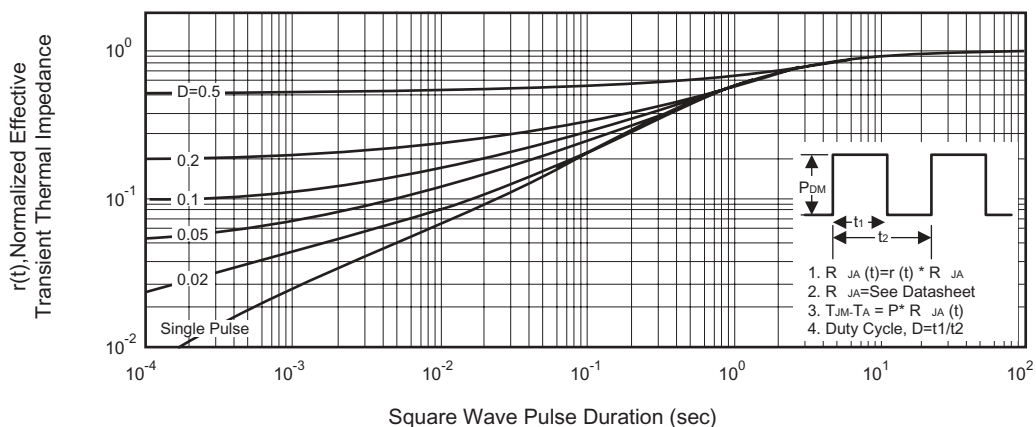


Figure 11. Normalized Thermal Transient Impedance Curve

## Ordering Information :

Device	Packing
Part Number-TP	Tape&Reel: 3Kpcs/Reel

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